

a transfer gate transistor including a second channel region having a second width and including a second gate insulator having a second thickness, a product of the first width and the second thickness being greater than or equal to a product of the second width and the first thickness.

REMARKS

Claims 1 – 22 are pending in this broadening reissue application.

The Applicants have amended claims 1, 4, 6, and 9 and have added new circuit claims 13 – 20 and new memory-cell claims 21 – 22 to broaden the scope of protection to their invention. The Applicants have also amended the drawings and specification to correct typographical errors.

The Applicants have added no new matter to the reissue application.

In light of the foregoing, original claims 2 – 3, 5, 7 – 8, and 10 – 12 as issued, claims 1, 4, 6, and 9 as amended, and new claims 13 – 22 are in condition for full allowance, and that action is respectfully requested.

If the Examiner believes that a phone interview would be helpful, he/she is respectfully requested to contact the Applicant's attorney, Bryan Santarelli, at (425) 455-5575.

DATED this 20th day of October, 2000.

Respectfully submitted,

GRAYBEAL JACKSON HALEY LLP



Bryan A. Santarelli

Attorney for Applicants

Registration No. 37,560

155-108th Avenue N.E., Ste 350

Bellevue, WA 98004-5901

(425) 455-5575

Enclosures